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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	90
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	112-BGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg890f512g-e-bga112r

1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32GG890 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (°C)	Package
EFM32GG890F512G-E-BGA112	512	128	48	1.98 - 3.8	-40 - 85	BGA112
EFM32GG890F1024G-E-BGA112	1024	128	48	1.98 - 3.8	-40 - 85	BGA112

Adding the suffix 'R' to the part number (e.g. EFM32GG890F512G-E-BGA112R) denotes tape and reel.

Visit **www.silabs.com** for information on global distributors and representatives.

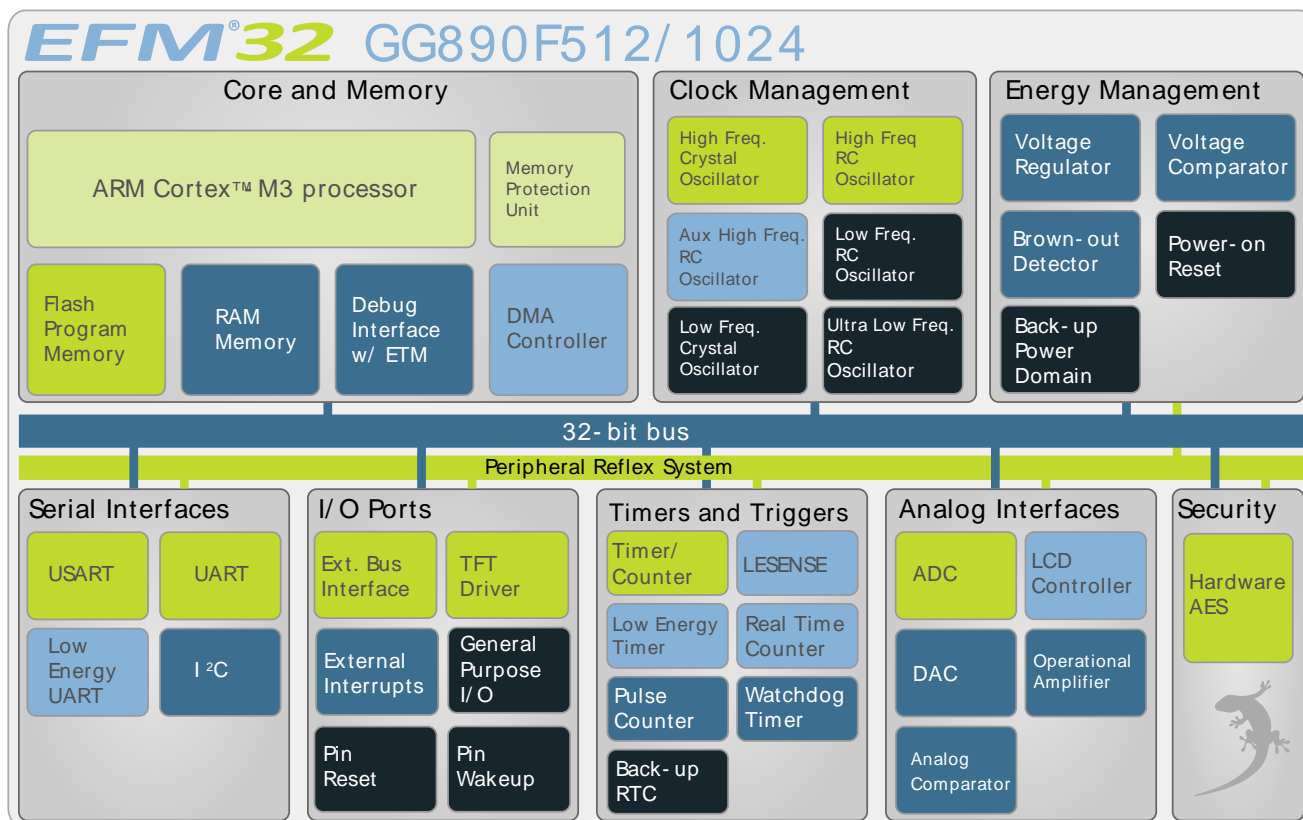
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M3, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32GG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32GG890 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32GG Reference Manual*.

A block diagram of the EFM32GG890 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M3 Core

The ARM Cortex-M3 includes a 32-bit RISC processor which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M3 is described in detail in *EFM32 Cortex-M3 Reference Manual*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and an Embedded Trace Module (ETM) for data/instruction tracing. In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.19 Backup Real Time Counter (BURTC)

The Backup Real Time Counter (BURTC) contains a 32-bit counter and is clocked either by a 32.768 kHz crystal oscillator, a 32.768 kHz RC oscillator or a 1 kHz ULFRCO. The BURTC is available in all Energy Modes and it can also run in backup mode, making it operational even if the main power should drain out.

2.1.20 Low Energy Timer (LETIMER)

The unique LETIMER[™], the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.21 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 - EM3.

2.1.22 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.23 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.24 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 8 external pins and 6 internal signals.

2.1.25 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has two single ended output buffers which can be combined into one differential output. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.26 Operational Amplifier (OPAMP)

The EFM32GG890 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

2.1.27 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSE[™]), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}\text{C}$ and $V_{DD}=3.0\text{ V}$, as defined in Table 3.2 (p. 10), unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150	$^{\circ}\text{C}$
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	$^{\circ}\text{C}$
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		$V_{DD}+0.3$	V
I_{IOMAX}	Current per I/O pin (sink)				100	mA
	Current per I/O pin (source)				-100	mA

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	$^{\circ}\text{C}$
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		\times^1		25	pF
DC_{LFXO}	Duty cycle		48	50	53.5	%
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

¹See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

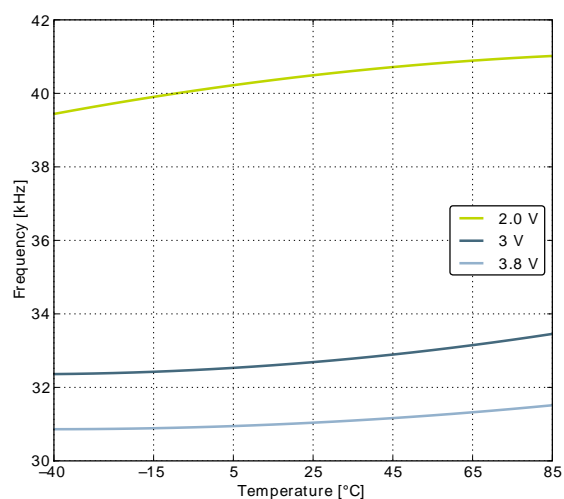
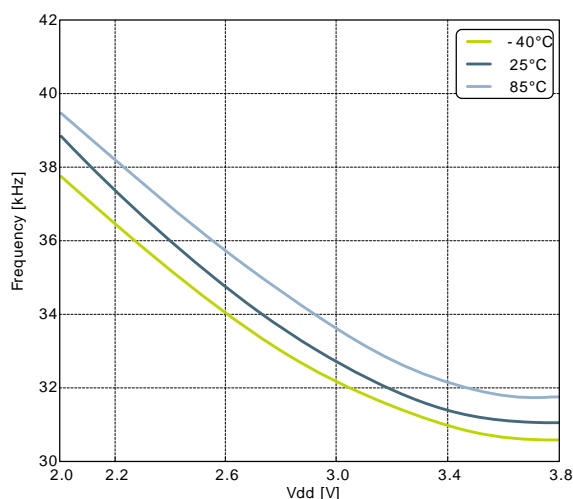
Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		48	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 48 MHz			50	Ohm
		Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L =20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μ A
		32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		μ A
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		μ s

3.9.3 LFRCO

Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$		31.29	32.768	34.28	kHz
t_{LFRCO}	Startup time not including software calibration			150		μs
I_{LFRCO}	Current consumption			300	900	nA
$\text{TUNESTEP}_{\text{LFRCO}}$	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.10. Calibrated LFRCO Frequency vs Temperature and Supply Voltage



3.9.4 HFRCO

Table 3.11. HFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48 ¹	6.60 ¹	6.72 ¹	MHz
		1 MHz frequency band	1.15 ²	1.20 ²	1.25 ²	MHz
$t_{\text{HFRCO_settling}}$	Settling time after start-up	$f_{\text{HFRCO}} = 14 \text{ MHz}$		0.6		Cycles
	Settling time after band switch			25		Cycles

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{HFRCO}	Current consumption (Production test condition = 14MHz)	$f_{\text{HFRCO}} = 28 \text{ MHz}$		165	190	μA
		$f_{\text{HFRCO}} = 21 \text{ MHz}$		134	155	μA
		$f_{\text{HFRCO}} = 14 \text{ MHz}$		106	120	μA
		$f_{\text{HFRCO}} = 11 \text{ MHz}$		94	110	μA
		$f_{\text{HFRCO}} = 6.6 \text{ MHz}$		77	90	μA
		$f_{\text{HFRCO}} = 1.2 \text{ MHz}$		25	32	μA
$\text{TUNESTEP}_{\text{HFRCO}}$	Frequency step for LSB change in TUNING value			0.3 ³		%

¹For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

²For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

³The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.11. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

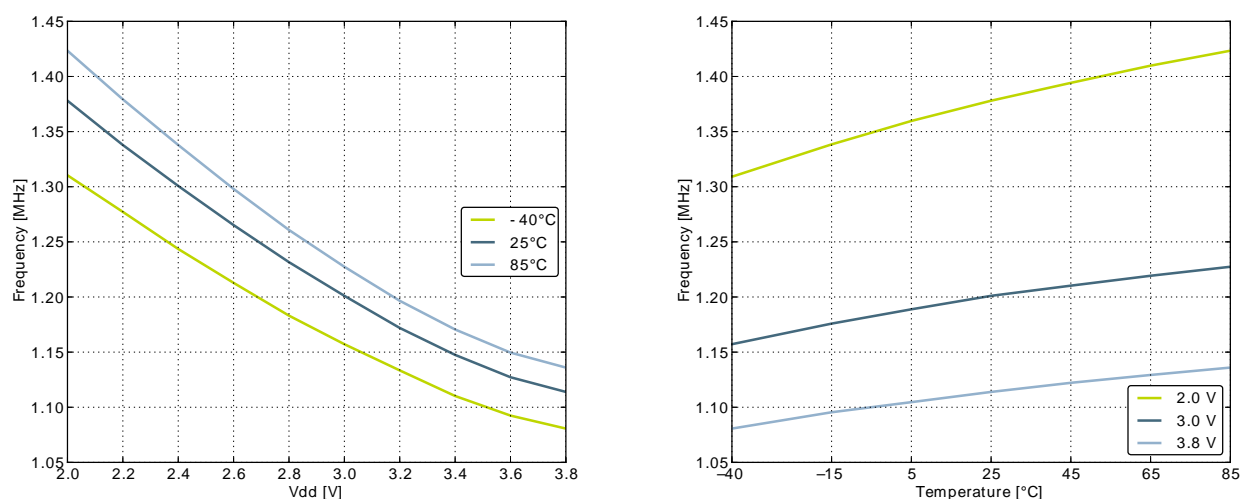
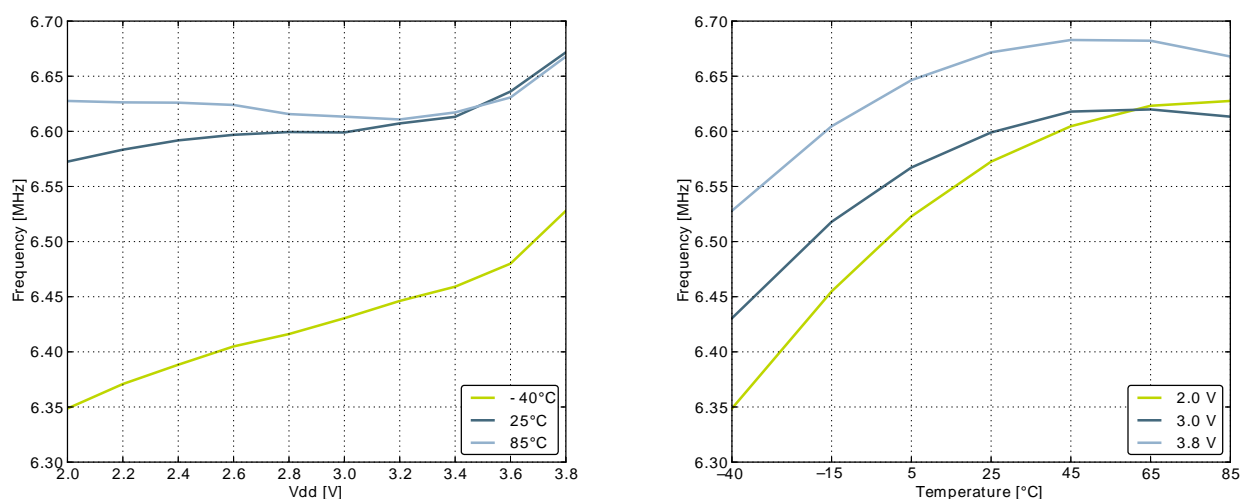


Figure 3.12. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature



Symbol	Parameter	Condition	Min	Typ	Max	Unit
		$V_{out}=1V$, RESSEL=0, 0.1 Hz<f<1 MHz, OPAXHCMDIS=0		196		μV_{RMS}
		$V_{out}=1V$, RESSEL=0, 0.1 Hz<f<1 MHz, OPAXHCMDIS=1		229		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAXHCMDIS=0		1230		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAXHCMDIS=1		2130		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAXHCMDIS=0		1630		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAXHCMDIS=1		2590		μV_{RMS}

Figure 3.25. OPAMP Common Mode Rejection Ratio

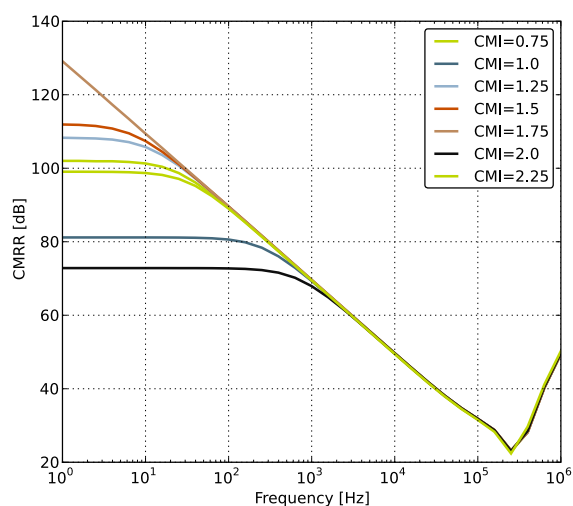
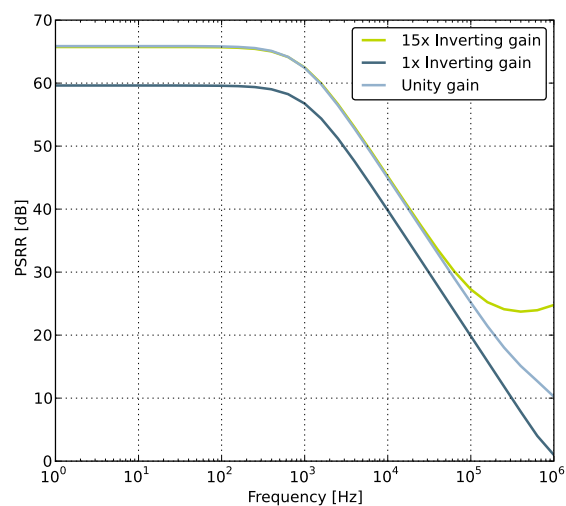


Figure 3.26. OPAMP Positive Power Supply Rejection Ratio



3.13 Analog Comparator (ACMP)

Table 3.17. ACMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULL-BIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.6	μA
		BIASPROG=0b1111, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	12	μA
		BIASPROG=0b1111, FULL-BIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		250	520	μA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		μA
		Internal voltage reference		5		μA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		43		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		78		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		111		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		145		kOhm
$t_{ACMPSTART}$	Startup time				10	μs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 43) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \quad (3.1)$$

3.14 Voltage Comparator (VCMP)

Table 3.18. VCMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{VCMPIN}	Input voltage range			V _{DD}		V
V _{VCMP_{CM}}	VCMP Common Mode voltage range			V _{DD}		V
I _{VCMP}	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	0.6	μA
		BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	30	μA
t _{VCMPREF}	Startup time reference generator	NORMAL		10		μs
V _{VCMP_{OFFSET}}	Offset voltage	Single ended	-230	-40	190	mV
		Differential		10		mV
V _{VCMPHYST}	VCMP hysteresis			40		mV
t _{VCMPSTART}	Startup time				10	μs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

$$V_{DD} \text{ Trigger Level} = 1.667V + 0.034 \times \text{TRIGLEVEL} \quad (3.2)$$

3.15 EBI

Figure 3.31. EBI Write Enable Timing

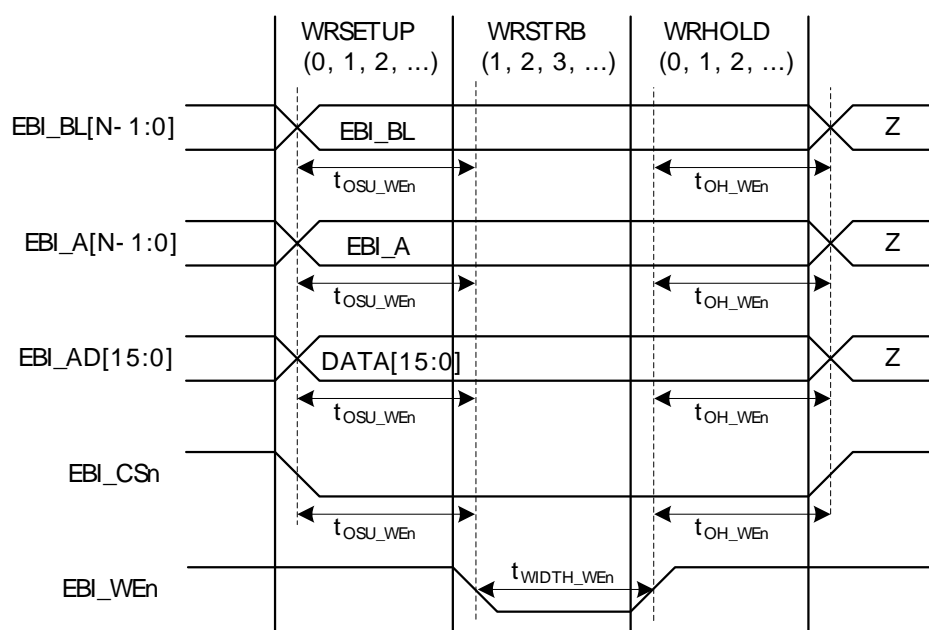


Table 3.19. EBI Write Enable Timing

Symbol	Parameter	Min	Typ	Max	Unit
$t_{OH_WEn}^{1\ 2\ 3\ 4}$	Output hold time, from trailing EBI_WEn/ EBI_NANDWEn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	$-6.00 + (WRHOLD * t_{HFCORECLK})$			ns
$t_{OSU_WEn}^{1\ 2\ 3\ 4\ 5}$	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_WEn/ EBI_NANDWEn edge	$-14.00 + (WRSETUP * t_{HFCORECLK})$			ns
$t_{WIDTH_WEn}^{1\ 2\ 3\ 4\ 5}$	EBI_WEn/EBI_NANDWEn pulse width	$-7.00 + ((WRSTRB + 1) * t_{HFCORECLK})$			ns

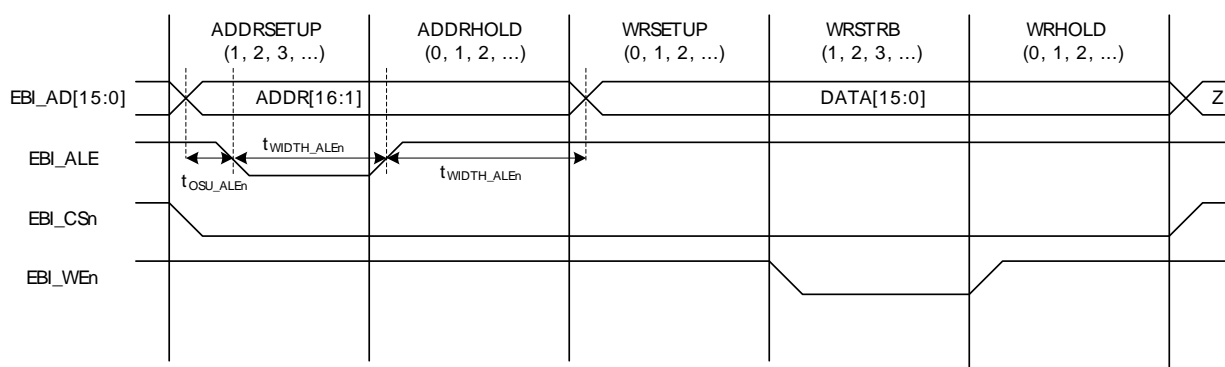
¹ Applies for all addressing modes (figure only shows D16 addressing mode)

² Applies for both EBI_WEn and EBI_NANWEn (figure only shows EBI_WEn)

³ Applies for all polarities (figure only shows active low signals)

⁴ Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

⁵ The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFWE=0. The leading edge of EBI_WEn can be moved to the right by setting HALFWE=1. This decreases the length of t_{WIDTH_WEn} and increases the length of t_{OSU_WEn} by $1/2 * t_{HFCLKNODIV}$.

Figure 3.32. EBI Address Latch Enable Related Output Timing**Table 3.20. EBI Address Latch Enable Related Output Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{OH_ALEn}^{1\ 2\ 3\ 4}$	Output hold time, from trailing EBI_ALE edge to EBI_AD invalid	$-6.00 + (ADDRHOLD^5 * t_{HFCORECLK})$			ns
$t_{OSU_ALEn}^{1\ 2\ 4}$	Output setup time, from EBI_AD valid to leading EBI_ALE edge	$-13.00 + (0 * t_{HFCORECLK})$			ns
$t_{WIDTH_ALEn}^{1\ 2\ 3\ 4}$	EBI_ALEn pulse width	$-7.00 + (ADDRSETUP + 1) * t_{HFCORECLK}$			ns

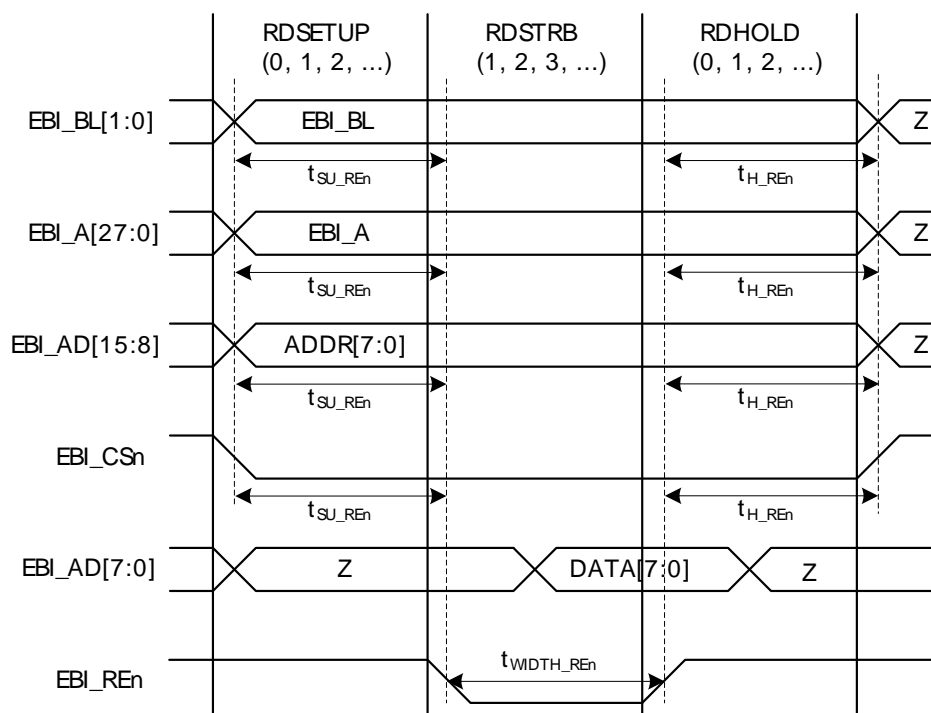
¹ Applies to addressing modes D8A24ALE and D16A16ALE (figure only shows D16A16ALE)

² Applies for all polarities (figure only shows active low signals)

³ The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFALE=0. The trailing edge of EBI_ALE can be moved to the left by setting HALFALE=1. This decreases the length of t_{WIDTH_ALEn} and increases the length of t_{OH_ALEn} by $t_{HFCORECLK} - 1/2 * t_{HFCLKNODIV}$.

⁴ Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

⁵ Figure only shows a write operation. For a multiplexed read operation the address hold time is controlled via the RDSETUP state instead of via the ADDRHOLD state.

Figure 3.33. EBI Read Enable Related Output Timing**Table 3.21. EBI Read Enable Related Output Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{OH_REn}^{1\ 2\ 3\ 4}$	Output hold time, from trailing EBI_REn/ EBI_NANDREn edge to EBI_AD, EBI_A, EBI_CS, EBI_BLn invalid	$-10.00 + (RDHOLD * t_{HFCORECLK})$			ns
$t_{OSU_REn}^{1\ 2\ 3\ 4\ 5}$	Output setup time, from EBI_AD, EBI_A, EBI_CS, EBI_BLn valid to leading EBI_REn/EBI_NANDREn edge	$-10.00 + (RDSETUP * t_{HFCORECLK})$			ns
$t_{WIDTH_REn}^{1\ 2\ 3\ 4\ 5\ 6}$	EBI_REn pulse width	$-9.00 + ((RDSTRB+1) * t_{HFCORECLK})$			ns

¹Applies for all addressing modes (figure only shows D8A8. Output timing for EBI_AD only applies to multiplexed addressing modes D8A24ALE and D16A16ALE)

²Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)

³Applies for all polarities (figure only shows active low signals)

⁴Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

⁵The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFRE=0. The leading edge of EBI_REn can be moved to the right by setting HALFRE=1. This decreases the length of t_{WIDTH_REn} and increases the length of t_{OSU_REn} by $1/2 * t_{HFCORECLK}$.

⁶When page mode is used, RDSTRB is replaced by RDPA for page hits.

3.17 I2C

Table 3.25. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f _{SCL}	SCL clock frequency	0		100 ¹	kHz
t _{LOW}	SCL clock low time	4.7			µs
t _{HIGH}	SCL clock high time	4.0			µs
t _{SU,DAT}	SDA set-up time	250			ns
t _{HD,DAT}	SDA hold time	8		3450 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	4.7			µs
t _{HD,STA}	(Repeated) START condition hold time	4.0			µs
t _{SU,STO}	STOP condition set-up time	4.0			µs
t _{BUF}	Bus free time between a STOP and START condition	4.7			µs

¹For the minimum HPPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32GG Reference Manual.

²The maximum SDA hold time (t_{HD,DAT}) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

³When transmitting data, this number is guaranteed only when $I2Cn_CLKDIV < ((3450 \cdot 10^{-9} [s] \cdot f_{HPPERCLK} [Hz]) - 4)$.

Table 3.26. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f _{SCL}	SCL clock frequency	0		400 ¹	kHz
t _{LOW}	SCL clock low time	1.3			µs
t _{HIGH}	SCL clock high time	0.6			µs
t _{SU,DAT}	SDA set-up time	100			ns
t _{HD,DAT}	SDA hold time	8		900 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	0.6			µs
t _{HD,STA}	(Repeated) START condition hold time	0.6			µs
t _{SU,STO}	STOP condition set-up time	0.6			µs
t _{BUF}	Bus free time between a STOP and START condition	1.3			µs

¹For the minimum HPPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32GG Reference Manual.

²The maximum SDA hold time (t_{HD,DAT}) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

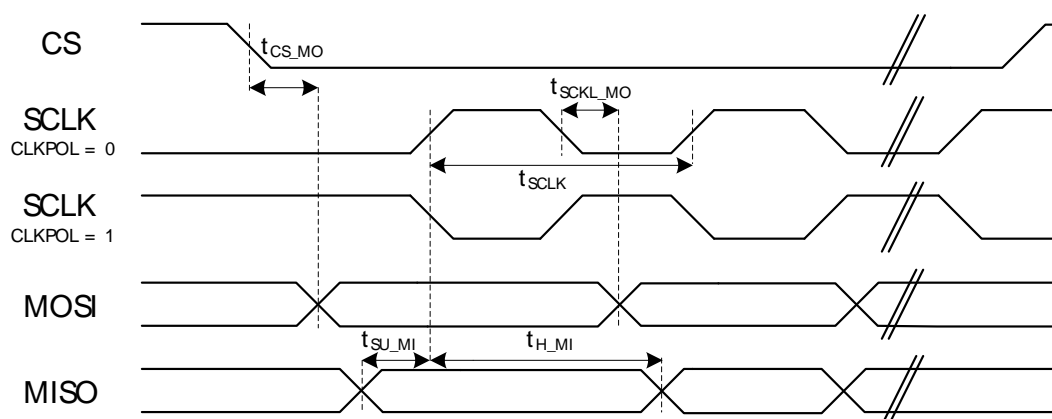
³When transmitting data, this number is guaranteed only when $I2Cn_CLKDIV < ((900 \cdot 10^{-9} [s] \cdot f_{HPPERCLK} [Hz]) - 4)$.

Table 3.27. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000 ¹	kHz
t_{LOW}	SCL clock low time	0.5			μ s
t_{HIGH}	SCL clock high time	0.26			μ s
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			μ s
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			μ s
$t_{SU,STO}$	STOP condition set-up time	0.26			μ s
t_{BUF}	Bus free time between a STOP and START condition	0.5			μ s

¹For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32GG Reference Manual.

3.18 USART SPI

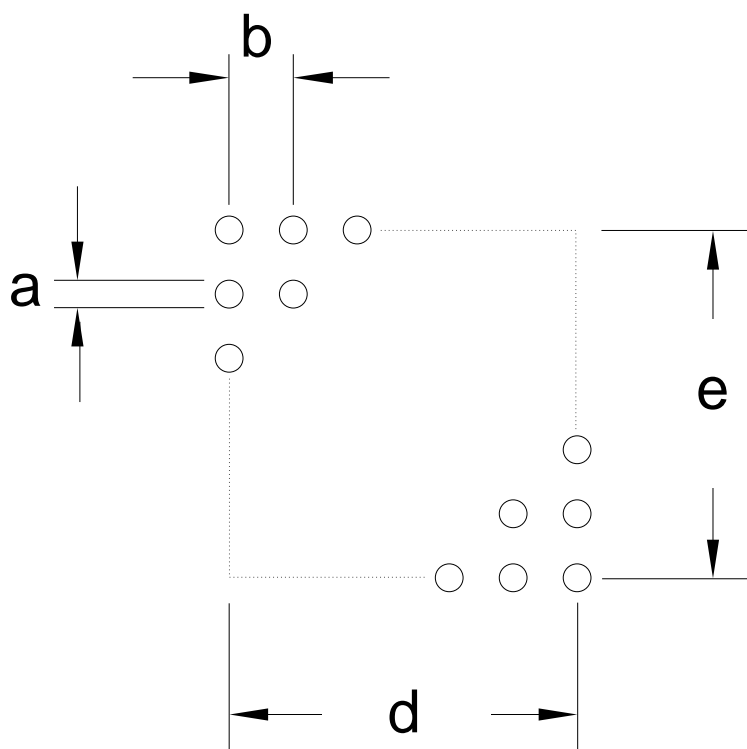
Figure 3.36. SPI Master Timing**Table 3.28. SPI Master Timing**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{SCLK}^{1\ 2}$	SCLK period		$2 * t_{HFPER-CLK}$			ns
$t_{CS_MO}^{1\ 2}$	CS to MOSI		-2.00		1.00	ns
$t_{SCLK_MO}^{1\ 2}$	SCLK to MOSI		-4.00		3.00	ns
$t_{SU_MI}^{1\ 2}$	MISO setup time	IOVDD = 1.98 V	36.00			ns
		IOVDD = 3.0 V	29.00			ns
$t_{H_MI}^{1\ 2}$	MISO hold time		-4.00			ns

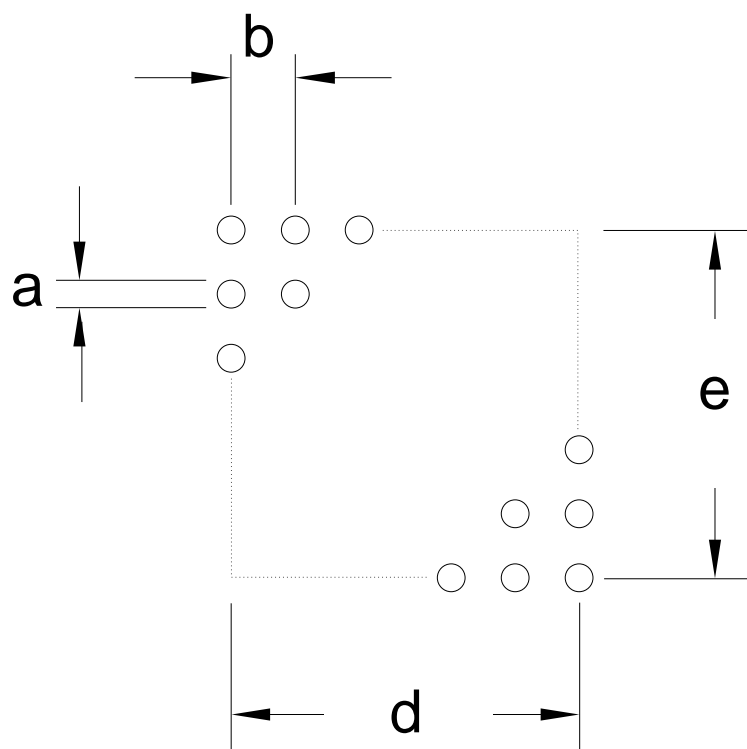
¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
EBI_AD02	PE10	PE10	PE10					External Bus Interface (EBI) address and data input / output pin 02.
EBI_AD03	PE11	PE11	PE11					External Bus Interface (EBI) address and data input / output pin 03.
EBI_AD04	PE12	PE12	PE12					External Bus Interface (EBI) address and data input / output pin 04.
EBI_AD05	PE13	PE13	PE13					External Bus Interface (EBI) address and data input / output pin 05.
EBI_AD06	PE14	PE14	PE14					External Bus Interface (EBI) address and data input / output pin 06.
EBI_AD07	PE15	PE15	PE15					External Bus Interface (EBI) address and data input / output pin 07.
EBI_AD08	PA15	PA15	PA15					External Bus Interface (EBI) address and data input / output pin 08.
EBI_AD09	PA0	PA0	PA0					External Bus Interface (EBI) address and data input / output pin 09.
EBI_AD10	PA1	PA1	PA1					External Bus Interface (EBI) address and data input / output pin 10.
EBI_AD11	PA2	PA2	PA2					External Bus Interface (EBI) address and data input / output pin 11.
EBI_AD12	PA3	PA3	PA3					External Bus Interface (EBI) address and data input / output pin 12.
EBI_AD13	PA4	PA4	PA4					External Bus Interface (EBI) address and data input / output pin 13.
EBI_AD14	PA5	PA5	PA5					External Bus Interface (EBI) address and data input / output pin 14.
EBI_AD15	PA6	PA6	PA6					External Bus Interface (EBI) address and data input / output pin 15.
EBI_ALE	PF3	PC11	PC11					External Bus Interface (EBI) Address Latch Enable output.
EBI_ARDY	PF2	PF2	PF2					External Bus Interface (EBI) Hardware Ready Control input.
EBI_BL0	PF6	PF6	PF6					External Bus Interface (EBI) Byte Lane/Enable pin 0.
EBI_BL1	PF7	PF7	PF7					External Bus Interface (EBI) Byte Lane/Enable pin 1.
EBI_CS0	PD9	PD9	PD9					External Bus Interface (EBI) Chip Select output 0.
EBI_CS1	PD10	PD10	PD10					External Bus Interface (EBI) Chip Select output 1.
EBI_CS2	PD11	PD11	PD11					External Bus Interface (EBI) Chip Select output 2.
EBI_CS3	PD12	PD12	PD12					External Bus Interface (EBI) Chip Select output 3.
EBI_CSTFT	PA7	PA7	PA7					External Bus Interface (EBI) Chip Select output TFT.
EBI_DCLK	PA8	PA8	PA8					External Bus Interface (EBI) TFT Dot Clock pin.
EBI_DTEN	PA9	PA9	PA9					External Bus Interface (EBI) TFT Data Enable pin.
EBI_HSNC	PA11	PA11	PA11					External Bus Interface (EBI) TFT Horizontal Synchronization pin.
EBI_NANDREn	PC3	PC3	PC3					External Bus Interface (EBI) NAND Read Enable output.
EBI_NANDWEn	PC5	PC5	PC5					External Bus Interface (EBI) NAND Write Enable output.
EBI_REn	PF5	PF9	PF5					External Bus Interface (EBI) Read Enable output.
EBI_VSNC	PA10	PA10	PA10					External Bus Interface (EBI) TFT Vertical Synchronization pin.
EBI_WEn	PF4	PF8	PF4					External Bus Interface (EBI) Write Enable output.
ETM_TCLK	PD7	PF8	PC6	PA6				Embedded Trace Module ETM clock .
ETM_TD0	PD6	PF9	PC7	PA2				Embedded Trace Module ETM data 0.

Figure 5.2. BGA112 PCB Solder Mask**Table 5.2. BGA112 PCB Solder Mask Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)
a	0.48
b	0.80
d	8.00
e	8.00

Figure 5.3. BGA112 PCB Stencil Design**Table 5.3. BGA112 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)
a	0.33
b	0.80
d	8.00
e	8.00

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 67) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

Updated PCB Land Pattern, PCB Solder Mask and PCB Stencil Design figures.

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 0.98

May 25th, 2012

Corrected BGA solder balls material description.

Corrected EM3 current consumption in the Electrical Characteristics section.

7.8 Revision 0.96

February 28th, 2012

Added reference to errata document.

Corrected BGA112 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.9 Revision 0.95

September 28th, 2011

Flash configuration for Giant Gecko is now 1024KB or 512KB. For flash sizes below 512KB, see the Leopard Gecko Family.

Corrected operating voltage from 1.8 V to 1.85 V.

Added rising POR level to Electrical Characteristics section.

Updated Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup.

Added Gain error drift and Offset error drift to ADC table.

Added Opamp pinout overview.

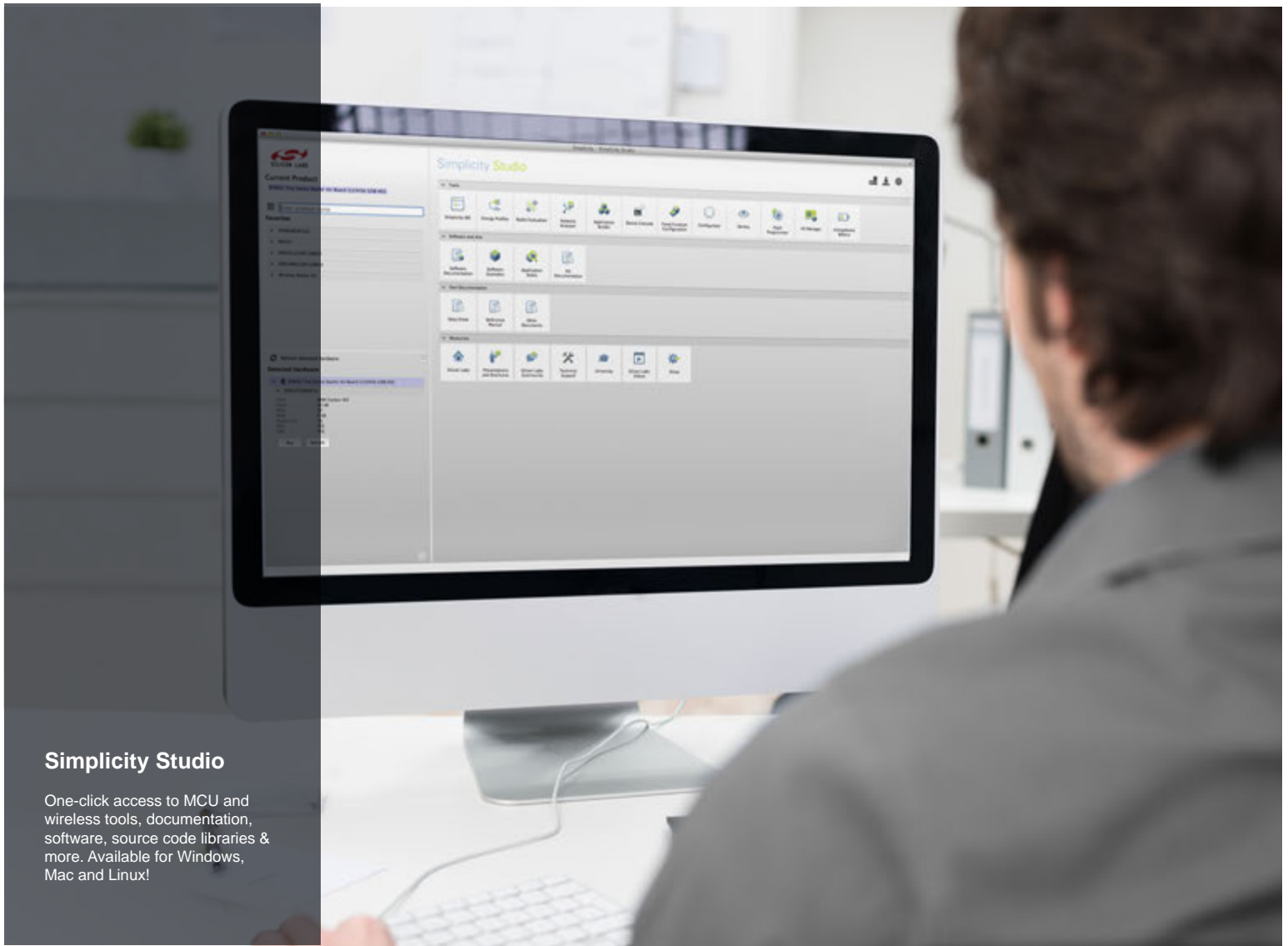
Added reference to errata document.

Corrected BGA112 package drawing.

Updated PCB land pattern, solder mask and stencil design.

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